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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	533MHz
Co-Processors/DSP	-
RAM Controllers	DDR
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	USB 2.0 + PHY (2)
Voltage - I/O	2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	672-LBGA
Supplier Device Package	672-LBGA (35x35)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8347vvajf

  - Programmable field size up to 2048 bits
  - Elliptic curve cryptography
  - F2m and F(p) modes
  - Programmable field size up to 511 bits
- Data encryption standard (DES) execution unit (DEU)
  - DES and 3DES algorithms
  - Two key (K1, K2) or three key (K1, K2, K3) for 3DES
  - ECB and CBC modes for both DES and 3DES
- Advanced encryption standard unit (AESU)
  - Implements the Rijndael symmetric-key cipher
  - Key lengths of 128, 192, and 256 bits
  - ECB, CBC, CCM, and counter (CTR) modes
- ARC four execution unit (AFEU)
  - Stream cipher compatible with the RC4 algorithm
  - 40- to 128-bit programmable key
- Message digest execution unit (MDEU)
  - SHA with 160- or 256-bit message digest
  - MD5 with 128-bit message digest
  - HMAC with either algorithm
- Random number generator (RNG)
- Four crypto-channels, each supporting multi-command descriptor chains
  - Static and/or dynamic assignment of crypto-execution units through an integrated controller
  - Buffer size of 256 bytes for each execution unit, with flow control for large data sizes

- Universal serial bus (USB) dual role controller
  - USB on-the-go mode with both device and host functionality
  - Complies with USB specification Rev. 2.0
  - Can operate as a stand-alone USB device
    - One upstream facing port
    - Six programmable USB endpoints
  - Can operate as a stand-alone USB host controller
    - USB root hub with one downstream-facing port
    - Enhanced host controller interface (EHCI) compatible
    - High-speed (480 Mbps), full-speed (12 Mbps), and low-speed (1.5 Mbps) operations
  - External PHY with UTMI, serial and UTMI+ low-pin interface (ULPI)
- Universal serial bus (USB) multi-port host controller
  - Can operate as a stand-alone USB host controller
    - USB root hub with one or two downstream-facing ports

3 Power Characteristics

The estimated typical power dissipation for the MPC8347E device is shown in Table 4.

Table 4. MPC8347E Power Dissipation[1]

	Core Frequency (MHz)	CSB Frequency (MHz)	Typical at T_J = 65	Typical[2,3]	Maximum[4]	Unit
PBGA	266	266	1.3	1.6	1.8	W
		133	1.1	1.4	1.6	W
	400	266	1.5	1.9	2.1	W
		133	1.4	1.7	1.9	W
	400	200	1.5	1.8	2.0	W
		100	1.3	1.7	1.9	W
TBGA	333	333	2.0	3.0	3.2	W
		166	1.8	2.8	2.9	W
	400	266	2.1	3.0	3.3	W
		133	1.9	2.9	3.1	W
	450	300	2.3	3.2	3.5	W
		150	2.1	3.0	3.2	W
	500	333	2.4	3.3	3.6	W
		166	2.2	3.1	3.4	W
	533	266	2.4	3.3	3.6	W
		133	2.2	3.1	3.4	W

1 The values do not include I/O supply power (OV_{DD}, LV_{DD}, GV_{DD}) or AV_{DD}. For I/O power values, see Table 5.

2 Typical power is based on a voltage of V_{DD} = 1.2 V, a junction temperature of T_J = 105°C, and a Dhrystone benchmark application.

3 Thermal solutions may need to design to a value higher than typical power based on the end application, T_A target, and I/O power.

4 Maximum power is based on a voltage of V_{DD} = 1.2 V, worst case process, a junction temperature of T_J = 105°C, and an artificial smoke test.

Table 5 shows the estimated typical I/O power dissipation for MPC8347E.

Table 5. MPC8347E Typical I/O Power Dissipation

Interface	Parameter	DDR2 GV_{DD} (1.8 V)	DDR1 GV_{DD} (2.5 V)	OV_{DD} (3.3 V)	LV_{DD} (3.3 V)	LV_{DD} (2.5 V)	Unit	Comments
DDR I/O 65% utilization 2.5 V Rs = 20 Ω Rt = 50 Ω 2 pair of clocks	200 MHz, 32 bits	—	0.42	—	—	—	W	—
	200 MHz, 64 bits	—	0.55	—	—	—	W	—
	266 MHz, 32 bits	—	0.5	—	—	—	W	—
	266 MHz, 64 bits	—	0.66	—	—	—	W	—
	300 MHz,[1] 32 bits	—	0.54	—	—	—	W	—
	300 MHz,[1] 64 bits	—	0.7	—	—	—	W	—
	333 MHz,[1] 32 bits	—	0.58	—	—	—	W	—
	333 MHz,[1] 64 bits	—	0.76	—	—	—	W	—
	400 MHz,[1] 32 bits	—	—	—	—	—		—
	400 MHz,[1] 64 bits	—	—	—	—	—		—
PCI I/O load = 30 pF	33 MHz, 32 bits	—	—	0.04	—	—	W	—
	66 MHz, 32 bits	—	—	0.07	—	—	W	—
Local bus I/O load = 25 pF	167 MHz, 32 bits	—	—	0.34	—	—	W	—
	133 MHz, 32 bits	—	—	0.27	—	—	W	—
	83 MHz, 32 bits	—	—	0.17	—	—	W	—
	66 MHz, 32 bits	—	—	0.14	—	—	W	—
	50 MHz, 32 bits	—	—	0.11	—	—	W	—
TSEC I/O load = 25 pF	MII	—	—	—	0.01	—	W	Multiply by number of interfaces used.
	GMII or TBI	—	—	—	0.06	—	W	
	RGMII or RTBI	—	—	—	—	0.04	W	
USB	12 MHz	—	—	0.01	—	—	W	Multiply by 2 if using 2 ports.
	480 MHz	—	—	0.2	—	—	W	
Other I/O		—	—	0.01	—	—	W	—

[1] TBGA package only.

Table 14. DDR SDRAM Output AC Timing Specifications for Source Synchronous Mode (continued)

At recommended operating conditions with GV_{DD} of 2.5 V ± 5%.

Parameter	Symbol[1]	Min	Max	Unit	Notes
MDQS epilogue end	t_{DDKLME}	-0.9	0.3	ns	7

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
2. All MCK/$\overline{\text{MCK}}$ referenced measurements are made from the crossing of the two signals ±0.1 V.
3. In the source synchronous mode, MCK/$\overline{\text{MCK}}$ can be shifted in 1/4 applied cycle increments through the clock control register. For the skew measurements referenced for t_{AOSKEW} it is assumed that the clock adjustment is set to align the address/command valid with the rising edge of MCK.
4. ADDR/CMD includes all DDR SDRAM output signals except MCK/$\overline{\text{MCK}}$, $\overline{\text{MCS}}$, and MDQ/MECC/MDM/MDQS. For the ADDR/CMD setup and hold specifications, it is assumed that the clock control register is set to adjust the memory clocks by 1/2 applied cycle.
5. Note that t_{DDKHMH} follows the symbol conventions described in note 1. For example, t_{DDKHMH} describes the DDR timing (DD) from the rising edge of the MCK(n) clock (KH) until the MDQS signal is valid (MH). t_{DDKHMH} can be modified through control of the DQSS override bits in the TIMING_CFG_2 register. In source synchronous mode, this will typically be set to the same delay as the clock adjust in the CLK_CNTL register. The timing parameters listed in the table assume that these 2 parameters have been set to the same adjustment value. See the *MPC8349E PowerQUICC™ II Pro Integrated Host Processor Family Reference Manual*, for a description and understanding of the timing modifications enabled by use of these bits.
6. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe should be centered inside of the data eye at the pins of the MPC8347E.
7. All outputs are referenced to the rising edge of MCK(n) at the pins of the MPC8347E. Note that t_{DDKHMP} follows the symbol conventions described in note 1.

Figure 5 shows the DDR SDRAM output timing for address skew with respect to any MCK.

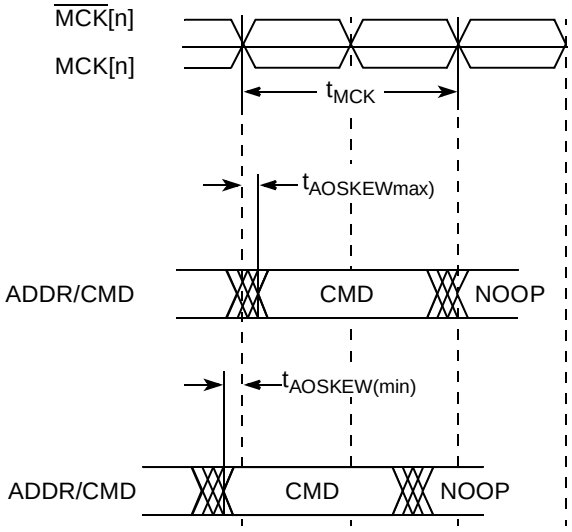


Figure 5. Timing Diagram for t_{AOSKEW} Measurement

Figure 6 provides the AC test load for the DDR bus.

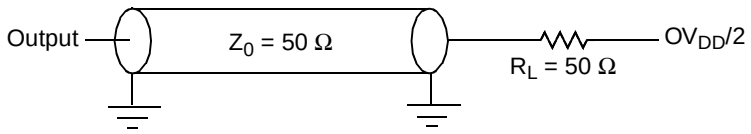


Figure 6. DDR AC Test Load

Table 15 shows the DDR SDRAM measurement conditions.

Table 15. DDR SDRAM Measurement Conditions

Symbol	DDR	Unit	Notes
V_{TH}	MV_{REF} ± 0.31 V	V	1
V_{OUT}	0.5 × GV_{DD}	V	2

Notes:
1. Data input threshold measurement point.
2. Data output measurement point.

Figure 7 shows the DDR SDRAM output timing diagram for source synchronous mode.

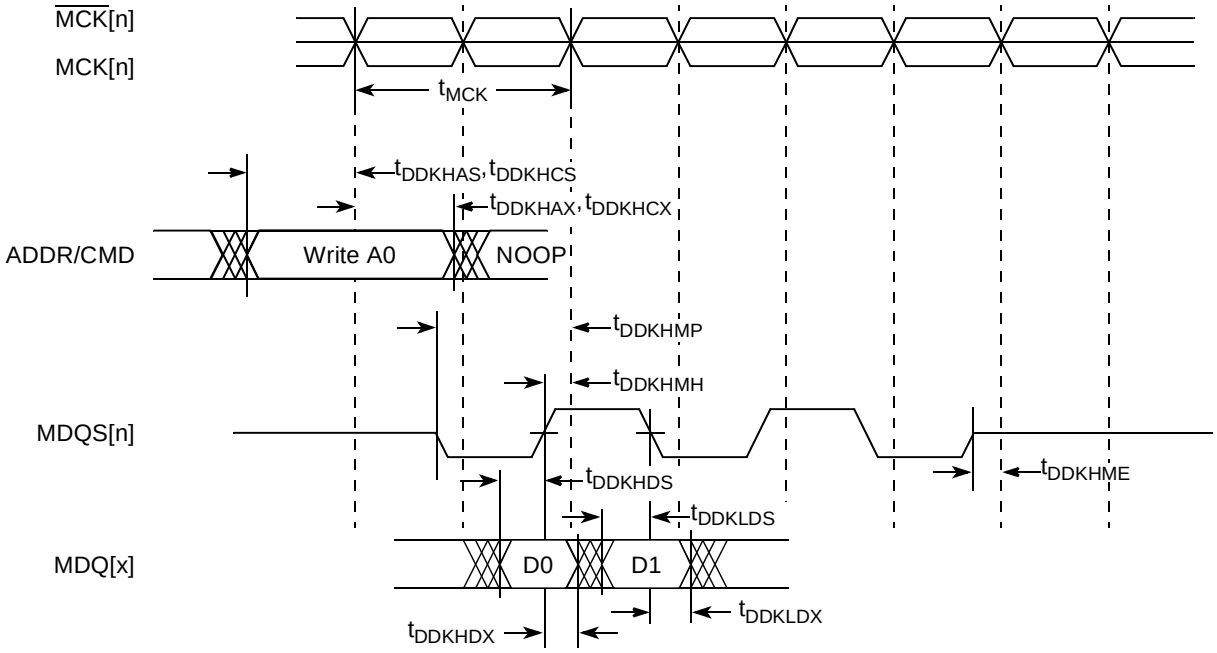


Figure 7. DDR SDRAM Output Timing Diagram for Source Synchronous Mode

Table 16 provides approximate delay information that can be expected for the address and command signals of the DDR controller for various loadings, which can be useful for a system utilizing the DLL. These numbers are the result of simulations for one topology. The delay numbers will strongly depend on the topology used. These delay numbers show the total delay for the address and command to arrive at the DRAM devices. The actual delay could be different than the delays seen in simulation, depending on the system topology. If a heavily loaded system is used, the DLL loop may need to be adjusted to meet setup requirements at the DRAM.

Figure 14 shows the TBI receive AC timing diagram.

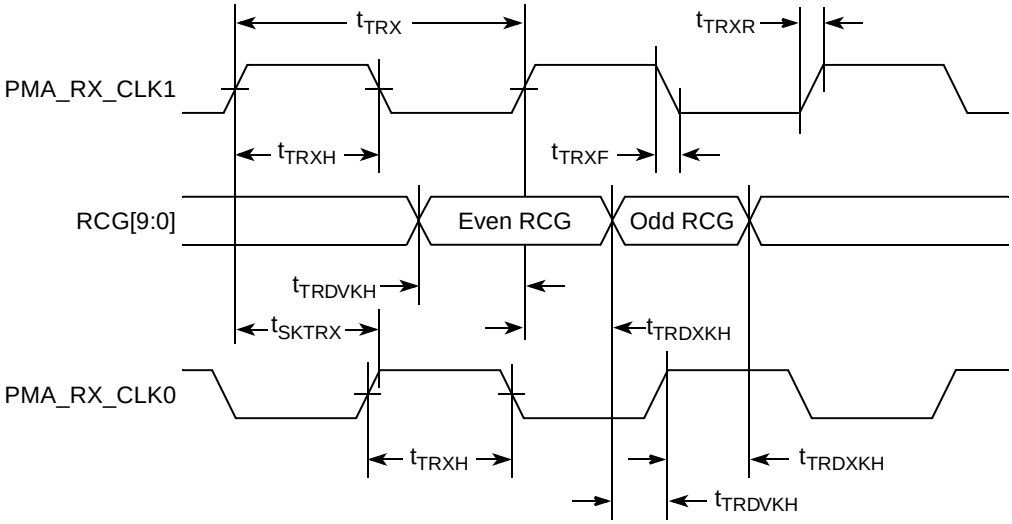


Figure 14. TBI Receive AC Timing Diagram

8.2.4 RGMII and RTBI AC Timing Specifications

Table 27 presents the RGMII and RTBI AC timing specifications.

Table 27. RGMII and RTBI AC Timing Specifications

At recommended operating conditions with LV_{DD} of 2.5 V ± 5%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit
Data to clock output skew (at transmitter)	t_{SKRGT}	–0.5	—	0.5	ns
Data to clock input skew (at receiver)[2]	t_{SKRGT}	1.0	—	2.8	ns
Clock cycle duration[3]	t_{RGT}	7.2	8.0	8.8	ns
Duty cycle for 1000Base-T[4, 5]	t_{RGTH}/t_{RGT}	45	50	55	%
Duty cycle for 10BASE-T and 100BASE-TX[3, 5]	t_{RGTH}/t_{RGT}	40	50	60	%
Rise time (20%–80%)	t_{RGTR}	—	—	0.75	ns
Fall time (20%–80%)	t_{RGTF}	—	—	0.75	ns
GTX_CLK125 reference clock period	t_{G12}[6]	—	8.0	—	ns
GTX_CLK125 reference clock duty cycle	t_{G125H}/t_{G125}	47	—	53	%

Notes:

1. In general, the clock reference symbol for this section is based on the symbols RGT to represent RGMII and RTBI timing. For example, the subscript of t_{RGT} represents the TBI (T) receive (RX) clock. Also, the notation for rise (R) and fall (F) times follows the clock symbol. For symbols representing skews, the subscript is SK followed by the clock being skewed (RGT).
2. This implies that PC board design requires clocks to be routed so that an additional trace delay of greater than 1.5 ns is added to the associated clock signal.
3. For 10 and 100 Mbps, t_{RGT} scales to 400 ns ± 40 ns and 40 ns ± 4 ns, respectively.
4. Duty cycle may be stretched/shrunk during speed changes or while transitioning to a received packet clock domains as long as the minimum duty cycle is not violated and stretching occurs for no more than three t_{RGT} of the lowest speed transitioned.
5. Duty cycle reference is $LV_{DD}/2$.
6. This symbol represents the external GTX_CLK125 and does not follow the original symbol naming convention.

8.3 Ethernet Management Interface Electrical Characteristics

The electrical characteristics specified here apply to the MII management interface signals management data input/output (MDIO) and management data clock (MDC). The electrical characteristics for GMII, RGMII, TBI and RTBI are specified in Section 8.1, "Three-Speed Ethernet Controller (TSEC)—GMII/MII/TBI/RGMII/RTBI Electrical Characteristics."

8.3.1 MII Management DC Electrical Characteristics

The MDC and MDIO are defined to operate at a supply voltage of 2.5 or 3.3 V. The DC electrical characteristics for MDIO and MDC are provided in Table 28 and Table 29.

Table 28. MII Management DC Electrical Characteristics Powered at 2.5 V

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage (2.5 V)	LV_{DD}	—		2.37	2.63	V
Output high voltage	V_{OH}	I_{OH} = –1.0 mA	LV_{DD} = Min	2.00	LV_{DD} + 0.3	V
Output low voltage	V_{OL}	I_{OL} = 1.0 mA	LV_{DD} = Min	GND – 0.3	0.40	V
Input high voltage	V_{IH}	—	LV_{DD} = Min	1.7	—	V
Input low voltage	V_{IL}	—	LV_{DD} = Min	–0.3	0.70	V
Input high current	I_{IH}	V_{IN}[1] = LV_{DD}		—	10	µA
Input low current	I_{IL}	V_{IN} = LV_{DD}		–15	—	µA

Note:

1. The symbol V_{IN}, in this case, represents the LV_{IN} symbol referenced in Table 1 and Table 2.

Table 29. MII Management DC Electrical Characteristics Powered at 3.3 V

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage (3.3 V)	LV_{DD}	—		2.97	3.63	V
Output high voltage	V_{OH}	I_{OH} = –1.0 mA	LV_{DD} = Min	2.10	LV_{DD} + 0.3	V
Output low voltage	V_{OL}	I_{OL} = 1.0 mA	LV_{DD} = Min	GND	0.50	V
Input high voltage	V_{IH}	—		2.00	—	V
Input low voltage	V_{IL}	—		—	0.80	V
Input high current	I_{IH}	LV_{DD} = Max	V_{IN}[1] = 2.1 V	—	40	µA
Input low current	I_{IL}	LV_{DD} = Max	V_{IN} = 0.5 V	–600	—	µA

Note:

1. The symbol V_{IN}, in this case, represents the LV_{IN} symbol referenced in Table 1 and Table 2.

8.3.2 MII Management AC Electrical Specifications

Table 30 provides the MII management AC timing specifications.

Table 30. MII Management AC Timing Specifications

At recommended operating conditions with LV_{DD} is 3.3 V ± 10% or 2.5 V ± 5%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit	Notes
MDC frequency	f_{MDC}	—	2.5	—	MHz	2
MDC period	t_{MDC}	—	400	—	ns	
MDC clock pulse width high	t_{MDCH}	32	—	—	ns	
MDC to MDIO delay	t_{MDKHDX}	10	—	170	ns	3
MDIO to MDC setup time	t_{MDDVKH}	5	—	—	ns	
MDIO to MDC hold time	t_{MDDXKH}	0	—	—	ns	
MDC rise time	t_{MDCR}	—	—	10	ns	
MDC fall time	t_{MDHF}	—	—	10	ns	

Notes:

1. The symbols for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MDKHDX} symbolizes management data timing (MD) for the time t_{MDC} from clock reference (K) high (H) until data outputs (D) are invalid (X) or data hold time. Also, t_{MDDVKH} symbolizes management data timing (MD) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MDC} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. This parameter is dependent on the csb_clk speed (that is, for a csb_clk of 267 MHz, the maximum frequency is 8.3 MHz and the minimum frequency is 1.2 MHz; for a csb_clk of 375 MHz, the maximum frequency is 11.7 MHz and the minimum frequency is 1.7 MHz).
3. This parameter is dependent on the csb_clk speed (that is, for a csb_clk of 267 MHz, the delay is 70 ns and for a csb_clk of 333 MHz, the delay is 58 ns).

Figure 16 shows the MII management AC timing diagram.

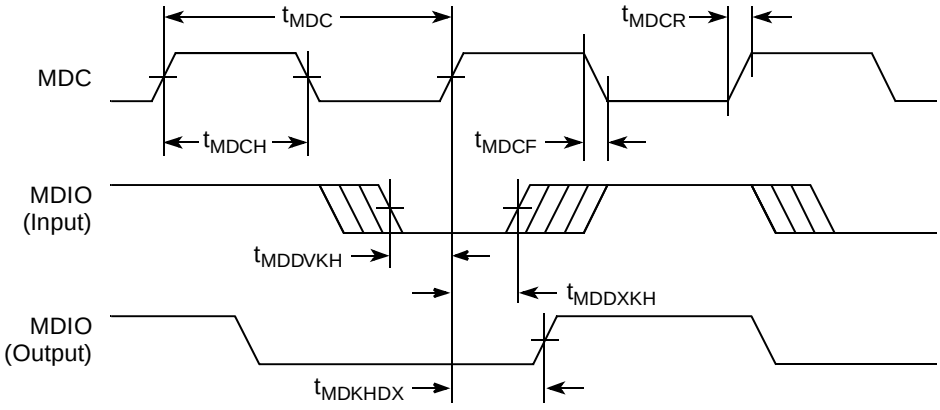


Figure 16. MII Management Interface Timing Diagram

Figure 17 and Figure 18 provide the AC test load and signals for the USB, respectively.

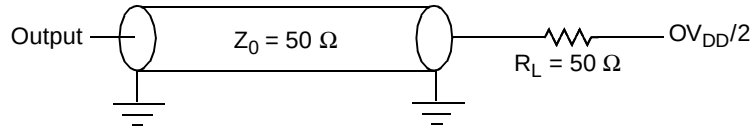


Figure 17. USB AC Test Load

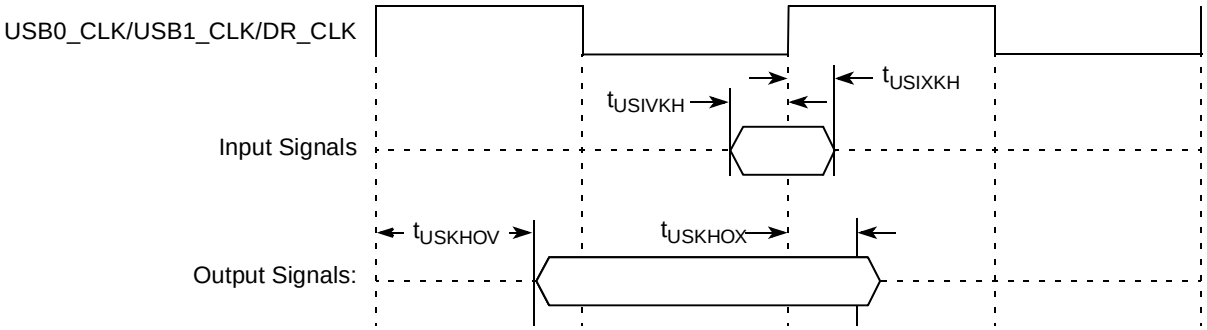


Figure 18. USB Signals

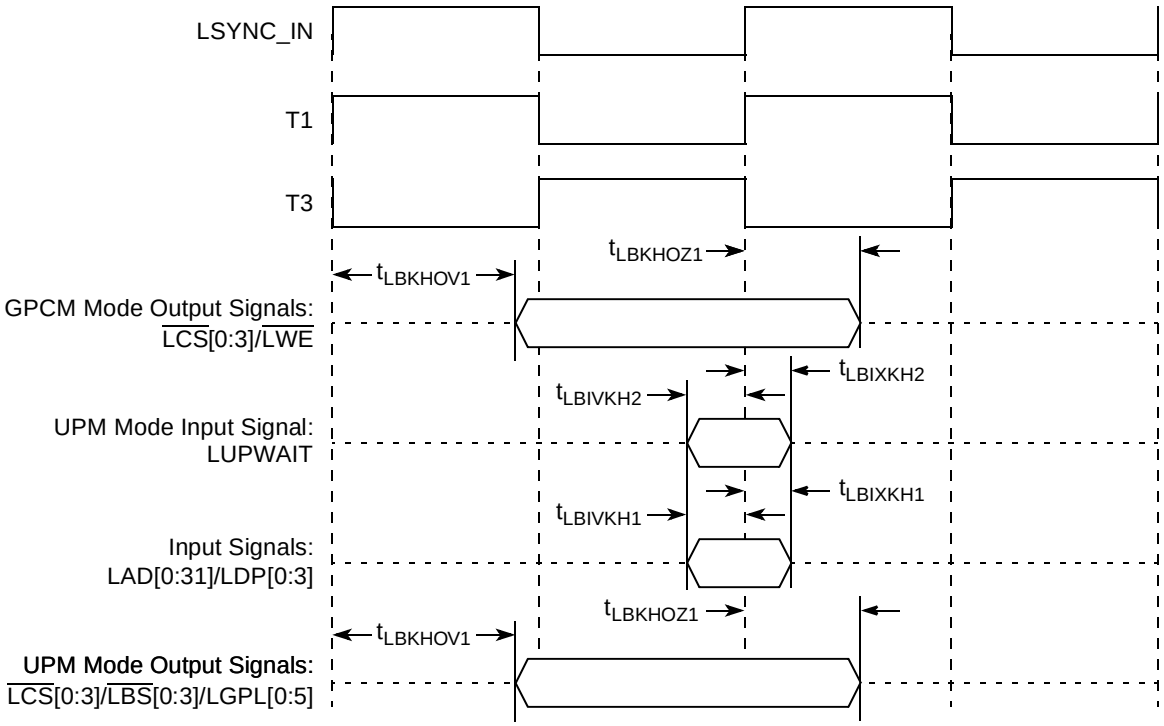


Figure 22. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 2 (DLL Enabled)

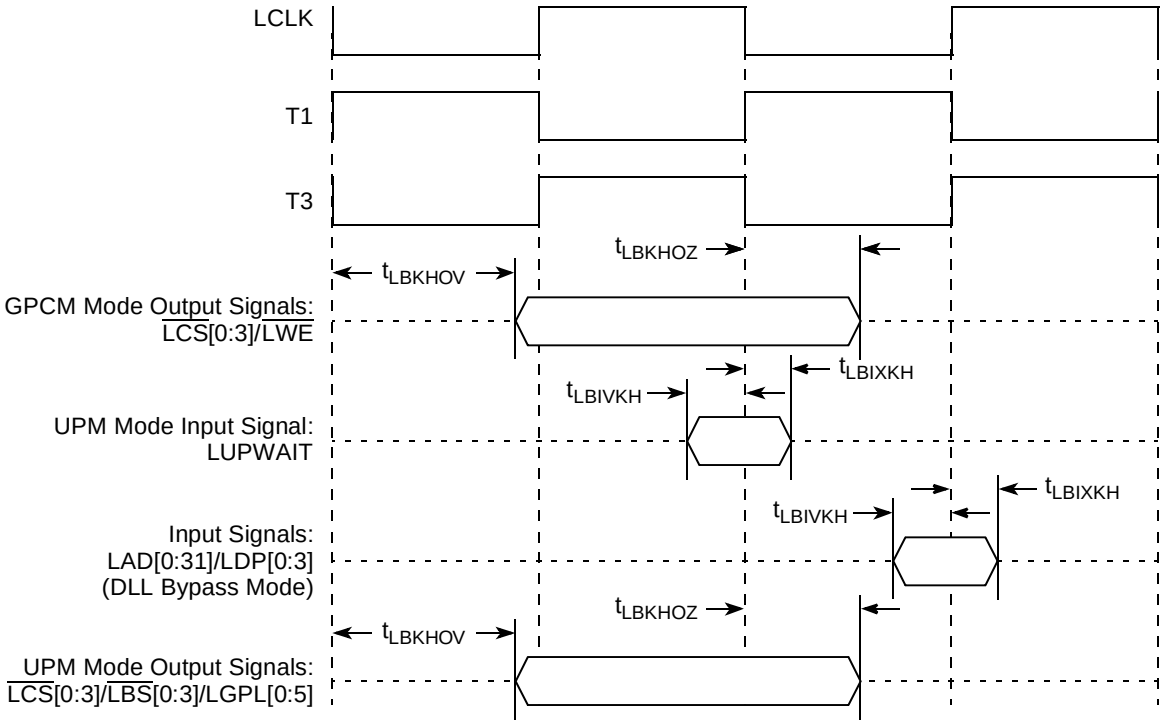


Figure 23. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 2 (DLL Bypass Mode)

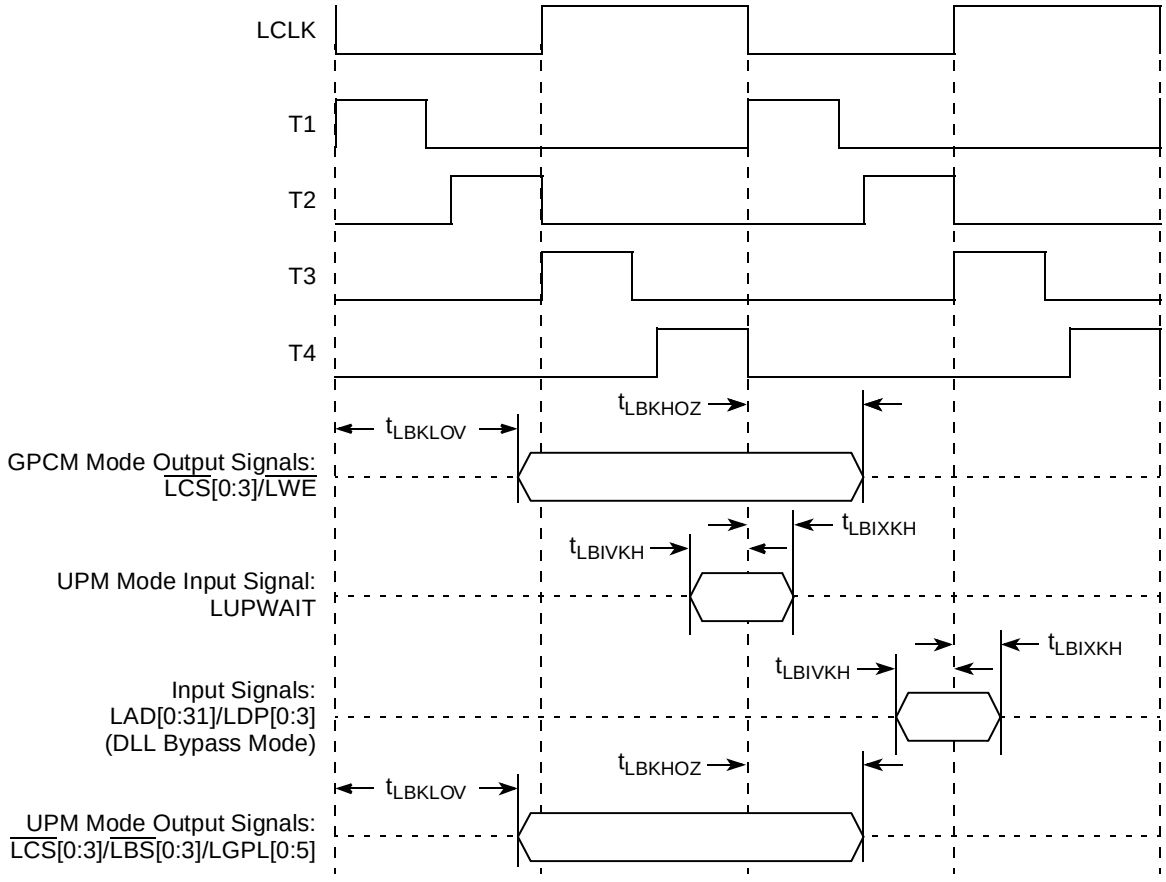


Figure 24. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 4 (DLL Bypass Mode)

Figure 34 shows the PCI input AC timing diagram.

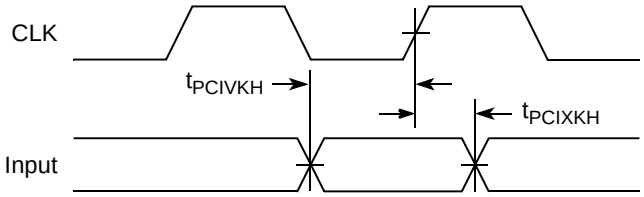


Figure 34. PCI Input AC Timing Diagram

Figure 35 shows the PCI output AC timing diagram.

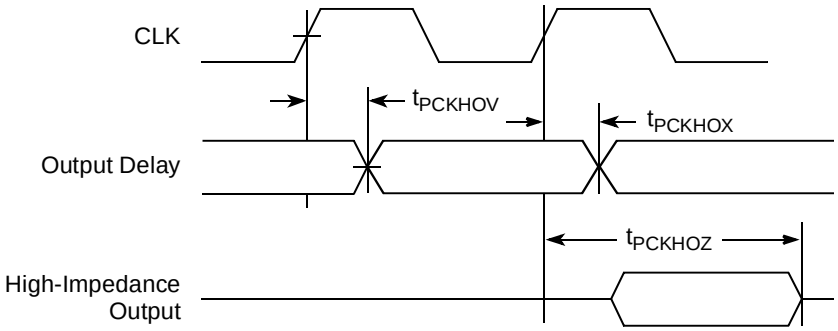


Figure 35. PCI Output AC Timing Diagram

Figure 36 provides the AC test load for the SPI.

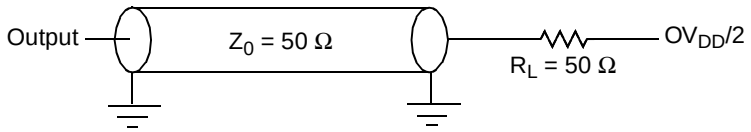
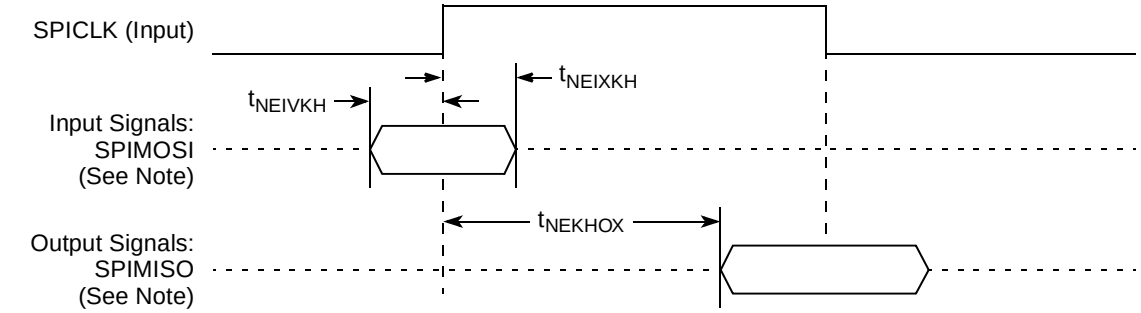


Figure 36. SPI AC Test Load

Figure 37 and Figure 38 represent the AC timings from Table 50. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.

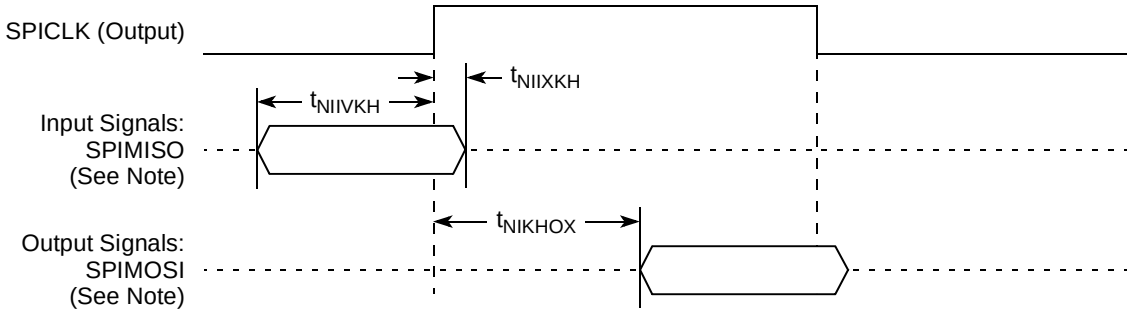
Figure 37 shows the SPI timings in slave mode (external clock).



Note: The clock edge is selectable on SPI.

Figure 37. SPI AC Timing in Slave Mode (External Clock) Diagram

Figure 38 shows the SPI timings in master mode (internal clock).

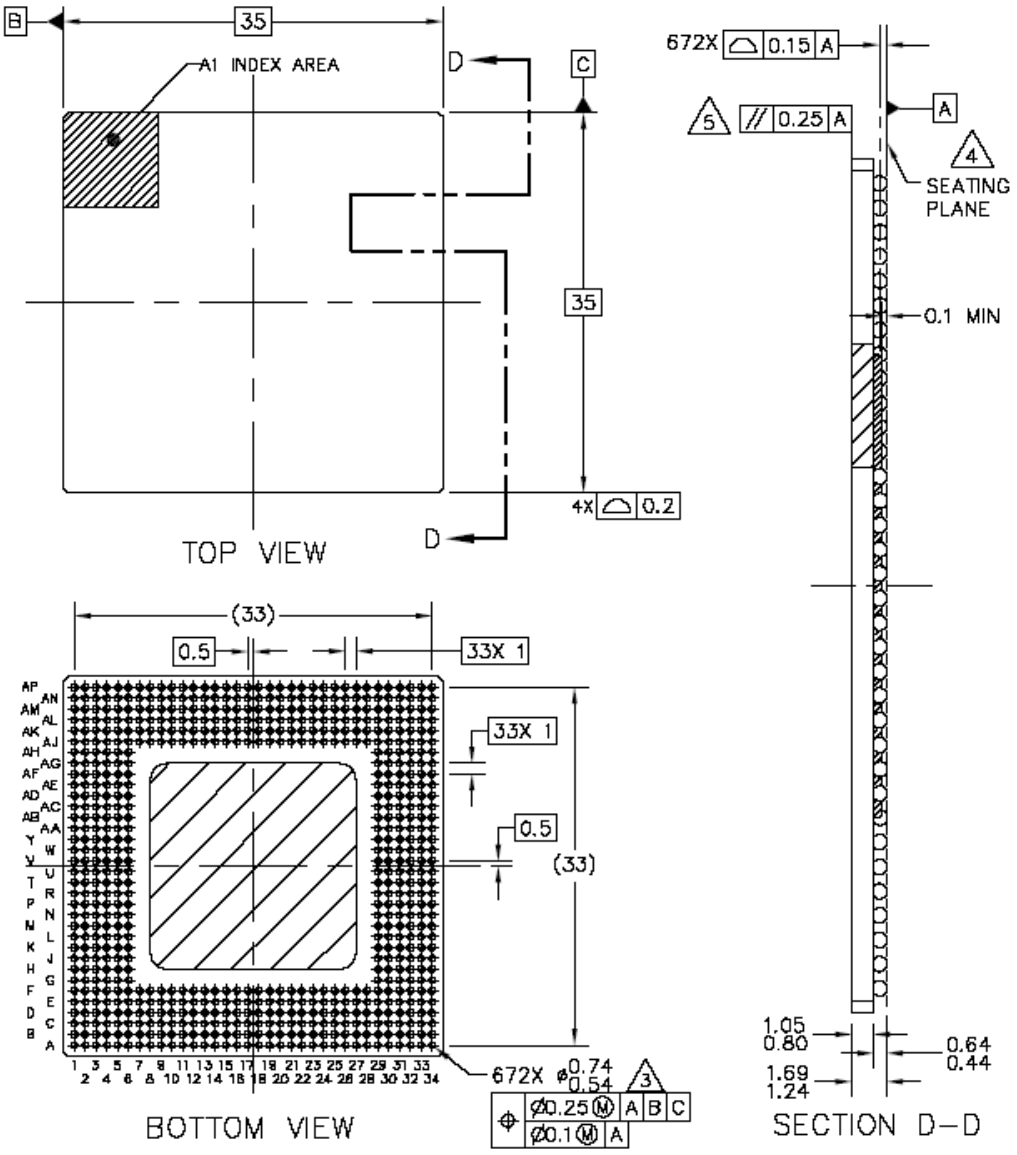


Note: The clock edge is selectable on SPI.

Figure 38. SPI AC Timing in Master Mode (Internal Clock) Diagram

18.2 Mechanical Dimensions for the MPC8347E TBGA

Figure 39 shows the mechanical dimensions and bottom surface nomenclature for the MPC8347E, 672-TBGA package.



Notes:

1.All dimensions are in millimeters.

2.Dimensions and tolerances per ASME Y14.5M-1994.

3.Maximum solder ball diameter measured parallel to datum A.

4.Datum A, the seating plane, is determined by the spherical crowns of the solder balls.

5.Parallelism measurement must exclude any effect of mark on top surface of package.

Figure 39. Mechanical Dimensions and Bottom Surface Nomenclature for the MPC8347E TBGA

18.5 Pinout Listings

Table 51 provides the pinout listing for the MPC8347E, 672 TBGA package.

Table 51. MPC8347E (TBGA) Pinout Listing

Signal	Package Pin Number	Pin Type	Power Supply	Notes
PCI				
PCI_INTA/IRQ_OUT	B34	O	OV_{DD}	2
PCI_RESET_OUT	C33	O	OV_{DD}	
PCI_AD[31:0]	G30, G32, G34, H31, H32, H33, H34, J29, J32, J33, L30, K31, K33, K34, L33, L34, P34, R29, R30, R33, R34, T31, T32, T33, U31, U34, V31, V32, V33, V34, W33, W34	I/O	OV_{DD}	
PCI_C/BE[3:0]	J30, M31, P33, T34	I/O	OV_{DD}	
PCI_PAR	P32	I/O	OV_{DD}	
PCI_FRAME	M32	I/O	OV_{DD}	5
PCI_TRDY	N29	I/O	OV_{DD}	5
PCI_IRDY	M34	I/O	OV_{DD}	5
PCI_STOP	N31	I/O	OV_{DD}	5
PCI_DEVSEL	N30	I/O	OV_{DD}	5
PCI_IDSEL	J31	I	OV_{DD}	
PCI_SERR	N34	I/O	OV_{DD}	5
PCI_PERR	N33	I/O	OV_{DD}	5
PCI_REQ[0]	D32	I/O	OV_{DD}	
PCI_REQ[1]/CPCI1_HS_ES	D34	I	OV_{DD}	
PCI_REQ[2:4]	E34, F32, G29	I	OV_{DD}	
PCI_GNT0	C34	I/O	OV_{DD}	
PCI_GNT1/CPCI1_HS_LED	D33	O	OV_{DD}	
PCI_GNT2/CPCI1_HS_ENUM	E33	O	OV_{DD}	
PCI_GNT[3:4]	F31, F33	O	OV_{DD}	
M66EN	A19	I	OV_{DD}	
DDR SDRAM Memory Interface				
MDQ[0:63]	D5, A3, C3, D3, C4, B3, C2, D4, D2, E5, G2, H6, E4, F3, G4, G3, H1, J2, L6, M6, H2, K6, L2, M4, N2, P4, R2, T4, P6, P3, R1, T2, AB5, AA3, AD6, AE4, AB4, AC2, AD3, AE6, AE3, AG4, AK5, AK4, AE2, AG6, AK3, AK2, AL2, AL1, AM5, AP5, AM2, AN1, AP4, AN5, AJ7, AN7, AM8, AJ9, AP6, AL7, AL9, AN8	I/O	GV_{DD}	

Table 52. MPC8347E (PBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
MPH0_D2_VMO_SE0/DR_D10_DPPD	B24	I/O	OV_{DD}	
MPH0_D3_SPEED/DR_D11_DMMD	A24	I/O	OV_{DD}	
MPH0_D4_DP/DR_D12_VBUS_VLD	D23	I/O	OV_{DD}	
MPH0_D5_DM/DR_D13_SESS_END	C23	I/O	OV_{DD}	
MPH0_D6_SER_RCV/DR_D14	B23	I/O	OV_{DD}	
MPH0_D7_DRVVBUS/DR_D15_IDPULLUP	A23	I/O	OV_{DD}	
MPH0_NXT/DR_RX_ACTIVE_ID	D22	I	OV_{DD}	
MPH0_DIR_DPPULLUP/DR_RESET	C22	I/O	OV_{DD}	
MPH0_STP_SUSPEND/DR_TX_READY	B22	I/O	OV_{DD}	
MPH0_PWRFAULT/DR_RX_VALIDH	A22	I	OV_{DD}	
MPH0_PCTL0/DR_LINE_STATE0	E21	I/O	OV_{DD}	
MPH0_PCTL1/DR_LINE_STATE1	D21	I/O	OV_{DD}	
MPH0_CLK/DR_RX_VALID	C21	I	OV_{DD}	
Programmable Interrupt Controller				
$\overline{\text{MCP\_OUT}}$	E8	O	OV_{DD}	2
$\overline{\text{IRQ}}$0/$\overline{\text{MCP_IN}}$/GPIO2[12]	J28	I/O	OV_{DD}	
$\overline{\text{IRQ}}$[1:5]/GPIO2[13:17]	K25, J25, H26, L24, G27	I/O	OV_{DD}	
$\overline{\text{IRQ}}$[6]/GPIO2[18]/CKSTOP_OUT	G28	I/O	OV_{DD}	
$\overline{\text{IRQ}}$[7]/GPIO2[19]/CKSTOP_IN	J26	I/O	OV_{DD}	
Ethernet Management Interface				
EC_MDC	Y24	O	LV_{DD1}	
EC_MDIO	Y25	I/O	LV_{DD1}	2
Gigabit Reference Clock				
EC_GTX_CLK125	Y26	I	LV_{DD1}	
Three-Speed Ethernet Controller (Gigabit Ethernet 1)				
TSEC1_COL/GPIO2[20]	M26	I/O	OV_{DD}	
TSEC1_CRS/GPIO2[21]	U25	I/O	LV_{DD1}	
TSEC1_GTX_CLK	V24	O	LV_{DD1}	3
TSEC1_RX_CLK	U26	I	LV_{DD1}	
TSEC1_RX_DV	U24	I	LV_{DD1}	
TSEC1_RX_ER/GPIO2[26]	L28	I/O	OV_{DD}	
TSEC1_RXD[7:4]/GPIO2[22:25]	M27, M28, N26, N27	I/O	OV_{DD}	
TSEC1_RXD[3:0]	W26, W24, Y28, Y27	I	LV_{DD1}	
TSEC1_TX_CLK	N25	I	OV_{DD}	

Table 52. MPC8347E (PBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
$AV_{DD}3$	AF9	Power for DDR DLL (1.2 V)	$AV_{DD}3$	
$AV_{DD}4$	U2	Power for LBIU DLL (1.2 V)	$AV_{DD}4$	
GND	A2, B1, B2, D10, D18, E6, E14, E22, F9, F12, F15, F18, F21, F24, G5, H6, J23, L4, L6, L12, L13, L14, L15, L16, L17, M11, M12, M13, M14, M15, M16, M17, M18, M23, N11, N12, N13, N14, N15, N16, N17, N18, P6, P11, P12, P13, P14, P15, P16, P17, P18, P24, R5, R11, R12, R13, R14, R15, R16, R17, R18, R23, T11, T12, T13, T14, T15, T16, T17, T18, U6, U11, U12, U13, U14, U15, U16, U17, U18, V12, V13, V14, V15, V16, V17, V23, V25, W4, Y6, AA23, AB24, AC5, AC8, AC11, AC14, AC17, AC20, AD9, AD15, AD21, AE12, AE18, AF3, AF26	—	—	
GV_{DD}	U9, V9, W10, W19, Y11, Y12, Y14, Y15, Y17, Y18, AA6, AB5, AC9, AC12, AC15, AC18, AC21, AC24, AD6, AD8, AD14, AD20, AE5, AE11, AE17, AG2, AG27	Power for DDR DRAM I/O voltage (2.5 V)	GV_{DD}	
$LV_{DD}1$	U20, W25	Power for three-speed Ethernet #1 and for Ethernet management interface I/O (2.5 V, 3.3 V)	$LV_{DD}1$	
$LV_{DD}2$	V20, Y23	Power for three-speed Ethernet #2 I/O (2.5 V, 3.3 V)	$LV_{DD}2$	
V_{DD}	J11, J12, J15, K10, K11, K12, K13, K14, K15, K16, K17, K18, K19, L10, L11, L18, L19, M10, M19, N10, N19, P9, P10, P19, R10, R19, R20, T10, T19, U10, U19, V10, V11, V18, V19, W11, W12, W13, W14, W15, W16, W17, W18	Power for core (1.2 V)	V_{DD}	
OV_{DD}	B27, D3, D11, D19, E15, E23, F5, F8, F11, F14, F17, F20, G24, H23, H24, J6, J14, J17, J18, K4, L9, L20, L23, L25, M6, M9, M20, P5, P20, P23, R6, R9, R24, U23, V4, V6	PCI, 10/100 Ethernet, and other standard (3.3 V)	OV_{DD}	

Table 58. CSB Frequency Options for Agent Mode

CFG_CLKIN_DIV at Reset[1]	SPMF	*csb_clk* : Input Clock Ratio[2]	Input Clock Frequency (MHz)[2]			
			16.67	25	33.33	66.67
			csb_clk Frequency (MHz)			
Low	0010	2 : 1				133
Low	0011	3 : 1			100	200
Low	0100	4 : 1		100	133	266
Low	0101	5 : 1		125	166	333
Low	0110	6 : 1	100	150	200	
Low	0111	7 : 1	116	175	233	
Low	1000	8 : 1	133	200	266	
Low	1001	9 : 1	150	225	300	
Low	1010	10 : 1	166	250	333	
Low	1011	11 : 1	183	275		
Low	1100	12 : 1	200	300		
Low	1101	13 : 1	216	325		
Low	1110	14 : 1	233			
Low	1111	15 : 1	250			
Low	0000	16 : 1	266			
High	0010	4 : 1		100	133	266
High	0011	6 : 1	100	150	200	
High	0100	8 : 1	133	200	266	
High	0101	10 : 1	166	250	333	
High	0110	12 : 1	200	300		
High	0111	14 : 1	233			
High	1000	16 : 1	266			

1 CFG_CLKIN_DIV doubles csb_clk if set high.

2 CLKIN is the input clock in host mode; PCI_CLK is the input clock in agent mode.
DDR2 memory may be used at 133 MHz provided that the memory components are specified for operation at this frequency.

19.2 Core PLL Configuration

RCWL[COREPLL] selects the ratio between the internal coherent system bus clock (*csb_clk*) and the e300 core clock (*core_clk*). Table 59 shows the encodings for RCWL[COREPLL]. COREPLL values that are not listed in Table 59 should be considered as reserved.

Table 66. Document Revision History (continued)

Revision	Date	Substantive Change(s)
8	2/2007	Page 1, updated first paragraph to reflect PowerQUICC II information. Updated note after second paragraph. In the features list in Section 1, "Overview," corrected DDR data rate to show: • 266 MHz for PBGA parts for all silicon revisions • 333 MHz for DDR for TBGA parts for silicon Rev. 1.x In Table 5, "MPC8347E Typical I/O Power Dissipation," added GV_{DD} 1.8-V values for DDR2; added table footnote to designate rates that apply only to the TBGA package. In Figure 43, "JTAG Interface Connection," updated with new figure. In Section 23, "Ordering Information," replicated note from document introduction. In Section 23.1, "Part Numbers Fully Addressed by This Document," replaced third sentence of first paragraph directing customer to product summary page for available frequency configuration parts. Updated back page information.
7	8/2006	Changed all references to revision 2.0 silicon to revision 3.0 silicon. Changed V_{IH} minimum value in Table 36, "JTAG Interface DC Electrical Characteristics," to OV_{DD} – 0.3. In Table 60, "Suggested PLL Configurations," deleted reference-number rows 902 and 703.
6	3/2006	Section 2, "Electrical Characteristics," moved to second section and all other section, table, and figure numbering change accordingly. Table 7, "CLKIN AC Timing Specifications:" Changed max rise and fall time from 1.2 to 2.3. Table 22, "GMII Receive AC Timing Specifications:" Changed min t_{TTKHDX} from 0.5 to 1.0. Table 30, "MII Management AC Timing Specifications:" Changed max value of t_{MDKHDX} from 70 to 170. Table 34, "Local Bus General Timing Parameters—DLL on:" Changed min $t_{LBIVKH2}$ from 1.7 to 2.2. Table 36, "JTAG interface DC Electrical Characteristics:" Changed V_{IH} input high voltage min to 2.0. Table 54, "Operating Frequencies for TBGA:" • Updated TBD values. • Changed maximum coherent system bus frequency for TBGA 667-MHz device to 333 MHz. Table 55, "Operating Frequencies for PBGA:" • Updated TBD values. • Changed PBGA maximum coherent system bus frequency to 266 MHz, and maximum DDR memory bus frequency to 133 MHz. Table 60, "Suggested PLL Configurations": Removed some values from suggested PLL configurations for reference numbers 902, 922, 903, and 923. Table 67, "Part Numbering Nomenclature": Updated TBD values in note 1. Added Table 68, "SVR Settings." Added Section 23.2, "Part Marking."
5	10/2005	In Table 57, updated AAVID 30x30x9.4 mm Pin Fin (natural convection) junction-to-ambient thermal resistance, from 11 to 10.
4	9/2005	Added Table 2, "MPC8347E Typical I/O Power Dissipation."
3	8/2005	Table 1: Updated values for power dissipation that were TBD in Revision 2.
2	5/2005	Table 1: Typical values for power dissipation are changed to TBD. Table 48: Footnote numbering was wrong. THERM0 should have footnote 9 instead of 8.

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